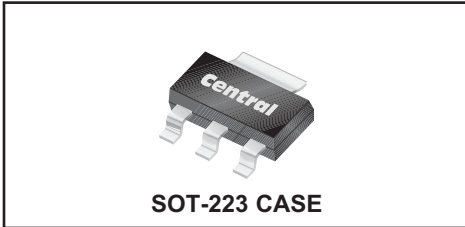


CZSH6-100C
SURFACE MOUNT
DUAL, COMMON CATHODE SILICON
SCHOTTKY POWER RECTIFIER
6 AMP, 100 VOLTS



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CZSH6-100C is manufactured with two 3 Amp Schottky rectifiers assembled in a common cathode configuration and packaged in a SOT-223 case. This device has been designed for high voltage applications requiring a low forward voltage drop.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
DC Blocking Voltage	V_R	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	70	V
Average Forward Current ($T_A=75^\circ\text{C}$)	I_O	6.0	A
Peak Forward Surge Current, $t_p=8.3\text{ms}$	I_{FSM}	75	A
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ\text{C}$ unless otherwise noted)

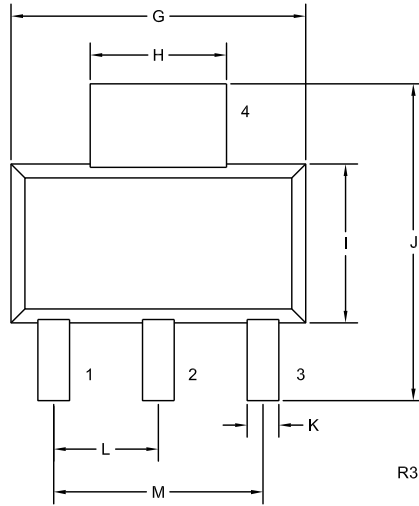
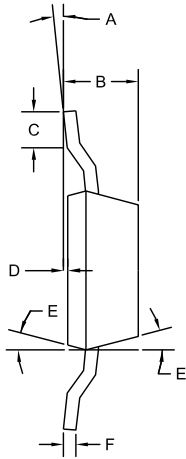
SYMBOL	TEST CONDITIONS	MAX	UNITS
I_R	$V_R=100\text{V}$	10	μA
I_R	$V_R=100\text{V}, T_A=100^\circ\text{C}$	20	mA
V_F	$I_F=1.0\text{A}$	0.7	V
V_F	$I_F=3.0\text{A}$	0.8	V
V_F	$I_F=6.0\text{A}$	1.0	V

CZSH6-100C

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6 AMP, 100 VOLTS**



SOT-223 CASE - MECHANICAL OUTLINE

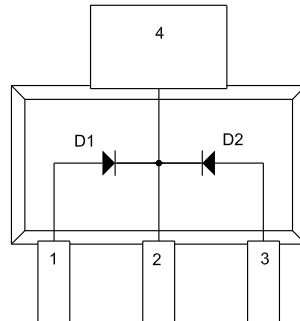


SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0°	10°	0°	10°
B	0.059	0.071	1.50	1.80
C	0.018	—	0.45	—
D	0.000	0.004	0.00	0.10
E	15°		15°	
F	0.009	0.014	0.23	0.35
G	0.248	0.264	6.30	6.70
H	0.114	0.122	2.90	3.10
I	0.130	0.146	3.30	3.70
J	0.264	0.287	6.70	7.30
K	0.024	0.033	0.60	0.85
L	0.091		2.30	
M	0.181		4.60	

SOT-223 (REV: R3)

R3

PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
 - 2) Cathode D1, D2
 - 3) Anode D2
 - 4) Cathode D1, D2
- Pin 2 and Pin 4 are common.

MARKING:

FULL PART NUMBER

R0 (22-November 2010)